



PATENT  
Customer No. 22,852  
Attorney Docket No. 07553.0017

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Mitsuru ISHIKAWA et al.

Application No.: 09/696,232 ✓

Filed: October 26, 2000

For: ETCHING METHOD

Commissioner for Patents  
Washington, DC 20231

Sir:

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) Group Art Unit: 1763  
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) Examiner: A. Olsen  
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AMENDMENT

In reply to the Office Action dated December 19, 2002, please amend the application as follows:

IN THE SPECIFICATION:

Page 2, please amend the paragraph beginning with "In order to" to read as follows:

(Amended) In order to achieve the object described above, in a first aspect of the present invention, ~~an etching method for etching an etching target film formed on a~~ substrate placed inside an airtight processing chamber by inducing a processing gas into the processing chamber, in which the processing gas contains at least CF<sub>4</sub> and N<sub>2</sub> and the etching target film is constituted of an upper organic film containing Si and a lower SiO<sub>2</sub> film, is provided. It is to be noted that the processing gas may further contain Ar.

FINNEGAN  
HENDERSON  
FARABOW  
GARRETT &  
DUNNER LLP

1300 I Street, NW  
Washington, DC 20005  
202.408.4000  
Fax 202.408.4400  
www.finnegan.com